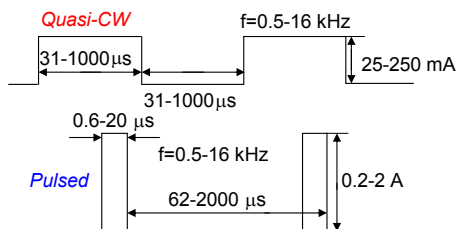
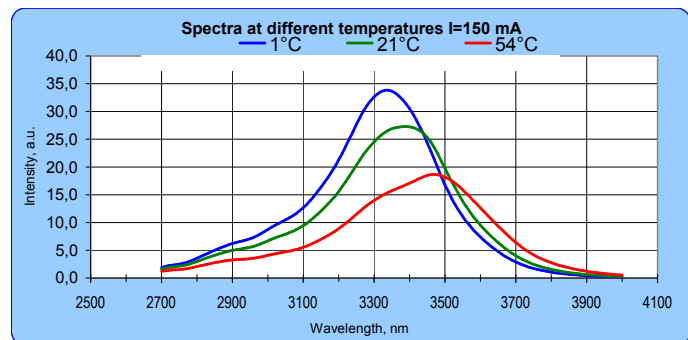
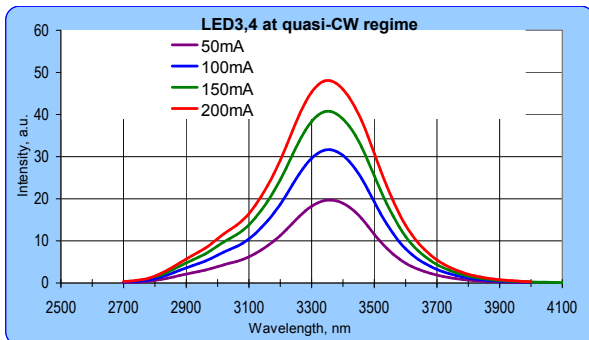
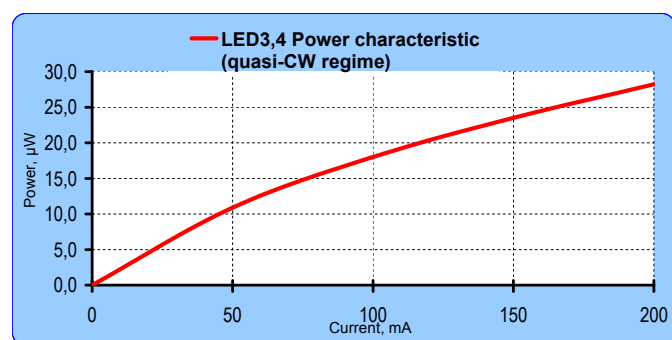
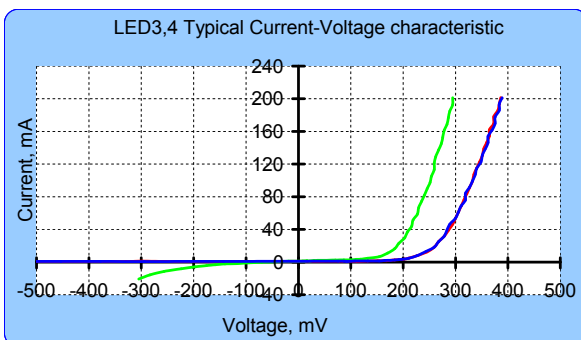
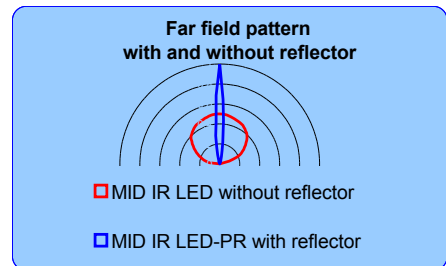
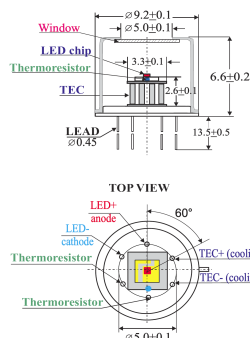


Light Emitting Diodes with central wavelength 3,40  $\mu\text{m}$  series are based on heterostructures grown on InAs substrates by MOCVD. InAs is used in the active layer. Wide band gap solid solutions InAsSbP with P content 50% are used for good electron confinement.

Parameters	Units	Conditions	Ratings		
			Min	Typ	Max
Peak emission wavelength	$\mu\text{m}$	T=300 K	3,32	3,40	3,46
FWHM of the emission band	nm	150 mA CW	400	500	600
Quasi-CW Optical Power	$\mu\text{W}$	200 mA qCW	25	35	45
Pulsed Optical Power	$\mu\text{W}$	1 A	320	400	480
Switching Time	ns	T=300 K	10	20	30
Operating Temperature Range, $^{\circ}\text{C}$	-240 $^{\circ}$ $\pm$ +50 $^{\circ}$				
Emitting Area, $\mu\text{m}$	300x300				
Soldering temperature	260 $^{\circ}\text{C}$				
Package					
TO-18 with a non-removable cap without a window			MID IR LED		
TO-18 with a parabolic reflector without a window			MID IR LED-PR		
TO-18 with a parabolic reflector with a window			MID IR LED-PRwin		
TO-5 with a built-in thermocooler and thermoresistor, covered by a cap with a window			<b>MID IR LED-TEC</b>		
TO-5 with a built-in thermocooler and thermoresistor, covered by a parabolic reflector with a window			MID IR LED-TEC-PR		



Maximum current is 220 mA at quasi-CW  
Maximum pulsed current is 1 A (duration 500 ns, repetition rate 2 kHz)  
Optimal operating current is 150-200 mA at quasi-CW.



**RELATED PRODUCTS**

**PD36 series Photodiodes** can be used for detecting LED emission

**LED driver with temperature controller DLT-37** can be used for LED power supply in quasi-CW and pulse modes

**LED driver with temperature controller DLT-27** can be used for LED power supply in quasi-CW and pulse modes at fixed frequency and pulse duration